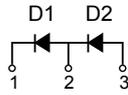
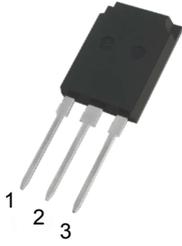
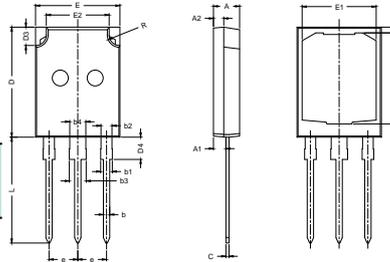


SDD80NXX

Discrete Diodes



Dimensions TO-247P



Dim.	Millimeter		Dim.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.85	5.10	D2	0.96	1.25
A1	2.31	2.51	D3	3.35	3.80
A2	1.85	2.10	D4	3.95	4.45
b	1.16	1.26	E	15.80	16.05
b1	/	2.25	E1	13.50	14.40
b2	1.96	2.15	E2	11.25	12.45
b3	/	3.25			
b4	2.96	3.15	e	5.44(BSC)	
c	0.59	0.66	L	19.80	20.25
D	20.85	21.10			
D1	17.15	17.75	R	1.90	2.10

	V_{RSM} V	V_{RRM} V
SDD80N01	200	100
SDD80N02	300	200
SDD80N04	500	400
SDD80N08	900	800
SDD80N10	1100	1000
SDD80N12	1300	1200
SDD80N16	1700	1600



Symbol	Test Conditions	Maximum Ratings	Unit
$I_{F(AV)M}$	$T_C=105^{\circ}C$; 180° sine, each Die	80 (For D1), 60 (For D2)	A
I_{FSM}	$T_{VJ}=45^{\circ}C$; $V_R=0V$; $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1710 (For D1), 1280 (For D2) 1880 (For D1), 1410 (For D2)	A
	$T_{VJ}=150^{\circ}C$; $V_R=0V$; $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1400 (For D1), 1050 (For D2) 1550 (For D1), 1160 (For D2)	
I^2t	$T_{VJ}=45^{\circ}C$; $V_R=0V$; $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	16000 (For D1), 12000 (For D2) 17140 (For D1), 12850 (For D2)	A^2s
	$T_{VJ}=150^{\circ}C$; $V_R=0V$; $t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	117700 (For D1), 8820 (For D2) 13700 (For D1), 10280 (For D2)	
T_{VJ} T_{VJM} T_{stg}		-40...+175 175 -55...+150	$^{\circ}C$
M_d	Mounting torque	0.8...1.2	Nm
Weight	Typical	6	g

Symbol	Test Conditions	Characteristic Values	Unit
I_R	$T_{VJ}=T_{VJM}$; $V_R=V_{RRM}$	< 3.00	mA
V_F	$I_F=80A$; $T_{VJ}=25^{\circ}C$	< 1.25	V
V_{FO}	For power-loss calculations only	0.80	V
r_F	$T_{VJ}=T_{VJM}$	3.0	m Ω
R_{thJC} R_{thCH}	DC current typical	0.33 0.20	K/W

